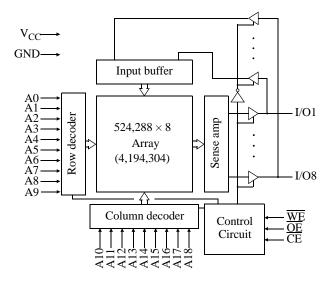


3.3V 512K × 8 CMOS SRAM

Features

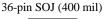
- Pin compatible to AS7C34096
- Industrial and commercial temperature
- Organization: 524,288 words × 8 bits
- Center power and ground pins
- High speed
 - 10/12/15/20 ns address access time
 - 4/5/6/7 ns output enable access time
- Low power consumption: ACTIVE
 - 650 mW / max @ 10 ns
- Low power consumption: STANDBY
 - 28.8 mW / max CMOS

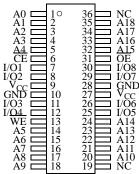
Logic block diagram

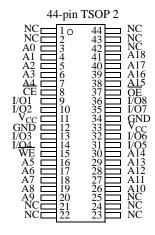


- Equal access and cycle times
- Easy memory expansion with \overline{CE} , \overline{OE} inputs
- TTL-compatible, three-state I/O
- JEDEC standard packages
 - 400 mil 36-pin SOJ
 - 44-pin TSOP 2
- ESD protection ≥ 2000 volts
- Latch-up current ≥ 200 mA

Pin arrangements







Selection guide

		-10	-12	-15	-20	Unit
Maximum address access time		10	12	15	20	ns
Maximum outputenable access time	4	5	6	7	ns	
Maximum operating current	Industrial	180	160	140	110	mA
Waximum operating current	Commercial	170	150	130	100	mA
Maximum CMOS standby current	8	8	8	8	mA	



Functional description

The AS7C34096A is a high-performance CMOS 4,194,304-bit Static Random Access Memory (SRAM) device organized as 524,288 words \times 8 bits. It is designed for memory applications where fast data access, low power, and simple interfacing are desired

Equal address access and cycle times (t_{AA} , t_{RC} , t_{WC}) of 10/12/15/20 ns with output enable access times (t_{OE}) of 4/5/6/7 ns are ideal for high-performance applications. The chip enable input \overline{CE} permits easy memory expansion with multiple-bank memory systems.

When $\overline{\text{CE}}$ is high the device enters standby mode. The device is guaranteed not to exceed 28.8mW power consumption in CMOS standby mode.

A write cycle is accomplished by asserting write enable (\overline{WE}) and chip enable (\overline{CE}) . Data on the input pins I/O1–I/O8 is written on the rising edge of \overline{WE} (write cycle 1) or \overline{CE} (write cycle 2). To avoid bus contention, external devices should drive I/O pins only after outputs have been disabled with output enable (\overline{OE}) or write enable (\overline{WE}) .

A read cycle is accomplished by asserting output enable (\overline{OE}) and chip enable (\overline{CE}) , with write enable (\overline{WE}) high. The chip drives I/O pins with the data word referenced by the input address. When either chip enable or output enable is inactive, or write enable is active, output drivers stay in high-impedance mode.

All chip inputs and outputs are TTL-compatible, and operation is from a single 3.3V supply voltage. This device is available as per industry standard 400-mil 36-pin SOJ and 44-pin TSOP 2 packages.

Absolute maximum ratings

Parameter	Symbol	Min	Max	Unit
Voltage on V _{CC} relative to GND	V _{t1}	-0.5	+5.0	V
Voltage on any pin relative to GND	V _{t2}	-0.5	V _{CC} +0.5	V
Power dissipation	P_{D}	_	1.0	W
Storage temperature (plastic)	T _{stg}	-65	+150	°C
Temperature with V _{CC} applied	T _{bias}	-55	+125	°C
DC current into output (low)	I_{OUT}	_	20	mA

NOTE: Stresses greater than those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions outside those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Truth table

CE	WE	ŌĒ	Data	Mode
Н	X	X	High Z	Standby (I _{SB} , I _{SB1})
L	Н	Н	High Z	Output disable (I _{CC})
L	Н	L	D _{OUT}	Read (I _{CC})
L	L	X	D _{IN}	Write (I _{CC})

Key: X = Don't care, L = Low, H = High



Recommended operating condition

Parame	eter	Symbol	Min	Nominal	Max	Unit
Supply voltage		V _{CC} (10/12/15/20)	3.0	3.3	3.6	V
Input voltage		V _{IH} **	2.0	_	$V_{CC} + 0.5$	V
		${ m V_{IL}}^*$	-0.5	_	0.8	V
Ambient operating commercial temperature industrial		T_{A}	0	_	70	°C
		T_{A}	-40	_	85	°C

DC operating characteristics (over the operating range) I

				-:	10	—]	12	-1	15	-2	20	
Parameter	Symbol	Test conditions		Min	Max	Min	Max	Min	Max	Min	Max	Unit
Input leakage current	$ I_{LI} $	$V_{CC} = Max$, $V_{IN} = GND$ to V_{CC}		_	1	1	1	ı	1	ı	1	μΑ
Output leakage current	$ I_{LO} $	$V_{CC} = Max, \overline{CE} = V_{IH}$ $V_{OUT} = GND \text{ to } V_{CC}$		_	1	1	1	-	1	1	1	μΑ
Operating power	L	$V_{CC} = Max, \overline{CE} \le V_{IL}$	Industrial	_	180	1	160	-	140	-	110	mA
supply current	supply current I_{CC}	$f = f_{Max}, I_{OUT} = 0mA$	Commercial	-	170	-	150	-	130	-	100	mA
	I_{SB}	$V_{CC} = Max, \overline{CE} \ge V_{IH}, f =$	f _{Max}	_	60	ı	60	ı	60	ı	60	mA
Standby power supply current	I_{SB1}	$V_{CC} = Max,$ $\overline{CE} \ge V_{CC} - 0.2V,$ $V_{IN} \le 0.2V \text{ or } V_{IN} \ge V_{CC} - 0.2V,$ $f = 0$		_	8	ı	8	1	8	-	8	mA
Output voltage	Output voltage			_	0.4	ı	0.4	ı	0.4	ı	0.4	V
Output Voltage				2.4	-	2.4	-	2.4	-	2.4	-	V

Capacitance (f = 1MHz, $T_a = 25^{\circ}$ C, $V_{CC} = NOMINAL)^2$

Parameter	Symbol	Signals	Test conditions	Max	Unit
Input capacitance	C _{IN}	$A, \overline{CE}, \overline{WE}, \overline{OE}$	$V_{IN} = 0V$	5	pF
I/O capacitance	C _{I/O}	I/O	$V_{IN} = V_{OUT} = 0V$	7	pF

 $[*]_{**}V_{IL}$ min = -1.0V for pulse width less than 5ns. V_{IH} max = V_{CC} + 2.0V for pulse width less than 5ns.



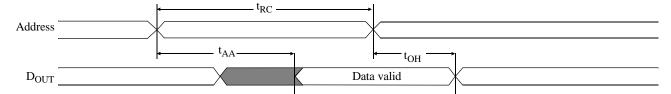
Read cycle (over the operating range)^{3,9}

		-3	10	-1	12	-3	15	-2	20		
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Unit	Notes
Read cycle time	t_{RC}	10	-	12	_	15	-	20	_	ns	
Address access time	t _{AA}	-	10	_	12	_	15	_	20	ns	3
Chip enable (\overline{CE}) access time	t _{ACE}	-	10	_	12	_	15	_	20	ns	3
Output enable (OE) access time	t _{OE}	_	4	_	5	_	6	_	7	ns	
Output hold from address change	t _{OH}	3	-	3	_	3	-	3	_	ns	5
CE Low to output in low Z	t _{CLZ}	3	-	3	_	3	-	3	_	ns	4, 5
CE High to output in high Z	t _{CHZ}	_	5	_	6	_	7	_	9	ns	4, 5
OE Low to output in low Z	t _{OLZ}	0	_	0	_	0	_	0	_	ns	4, 5
OE High to output in high Z	t _{OHZ}	_	5	_	6	_	7	_	9	ns	4, 5
Power up time	t_{PU}	0	_	0	_	0	_	0	_	ns	4, 5
Power down time	t _{PD}	-	10	1	12	_	15	_	20	ns	4, 5

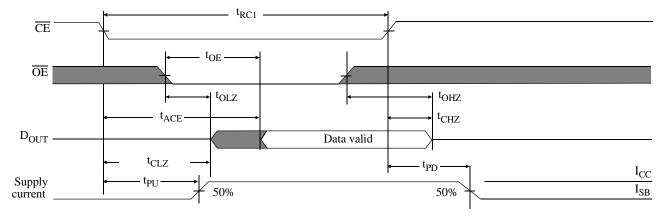
Key to switching waveforms

Rising input Falling input Undefined/don't care

Read waveform 1 (address controlled)^{3,6,7,9}



Read waveform 2 (CE, OE controlled)^{3,6,8,9}

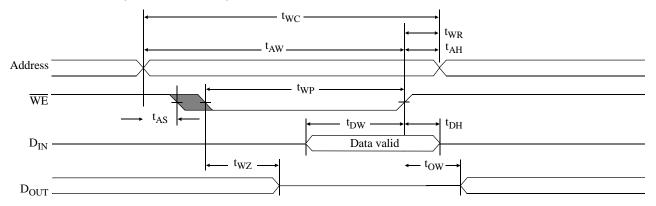




Write cycle (over the operating range) $^{I\theta}$

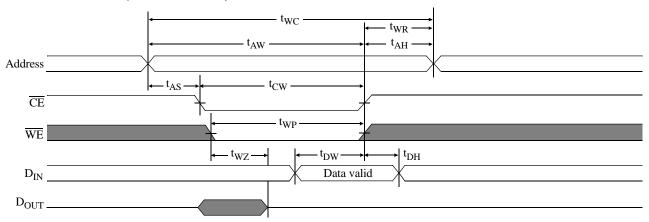
			10	-3	12	-3	15	-2	20		
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Unit	Notes
Write cycle time	t_{WC}	10	_	12	_	15	_	20	_	ns	
Chip enable (CE) to write end	t _{CW}	7	_	8	_	10	_	12	_	ns	
Address setup to write end	t _{AW}	7	_	8	_	10	_	12	_	ns	
Address setup time	t _{AS}	0	-	0	_	0	_	0	-	ns	
Write pulse width $(\overline{OE} = high)$	t _{WP1}	7	_	8	_	10	_	12	_	ns	
Write pulse width $(\overline{OE} = low)$	t _{WP2}	10	-	12	_	15	_	20	-	ns	
Address hold from end of write	t _{AH}	0	_	0	_	0	_	0	_	ns	
Write recovery time	t _{WR}	0	_	0	_	0	_	0	_	ns	
Data valid to write end	t_{DW}	5	-	6	_	7	_	9	-	ns	
Data hold time	t _{DH}	0	_	0	_	0	_	0	_	ns	4, 5
Write enable to output in high Z	t_{WZ}	0	5	0	6	0	7	0	9	ns	4, 5
Output active from write end	t _{OW}	3	_	3	_	3	_	3	_	ns	4, 5

Write waveform 1 ($\overline{\text{WE}}$ controlled)¹⁰



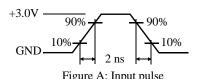


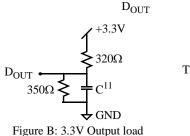
Write waveform 2 (CE controlled)10

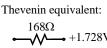


AC test conditions

- Output load: see Figure B.
- Input pulse level: GND to 3.0V. See Figures A and B.
- Input rise and fall times: 2 ns. See Figure A.
- Input and output timing reference levels: 1.5V.





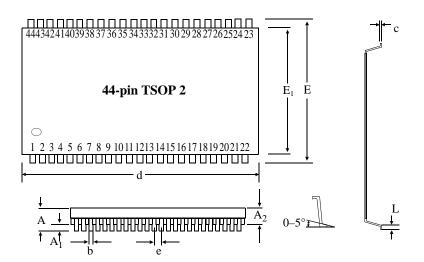


Notes

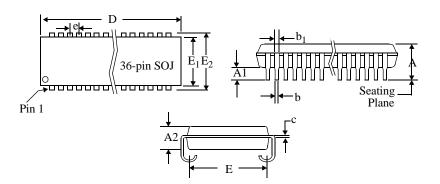
- 1 During V_{CC} power-up, a pull-up resistor to V_{CC} on \overline{CE} is required to meet I_{SB} specification.
- 2 This parameter is sampled, but not 100% tested.
- 3 For test conditions, see AC Test Conditions.
- 4 t_{CLZ} and t_{CHZ} are specified with $C_L = 5pF$ as in Figure B. Transition is measured ± 500 mV from steady-state voltage.
- 5 This parameter is guaranteed, but not tested.
- $\overline{\text{WE}}$ is HIGH for read cycle.
- 7 $\overline{\text{CE}}$ and $\overline{\text{OE}}$ are LOW for read cycle.
- 8 Address valid prior to or coincident with $\overline{\text{CE}}$ transition Low.
- 9 All read cycle timings are referenced from the last valid address to the first transitioning address.
- 10 All write cycle timings are referenced from the last valid address to the first transitioning address.
- 11 C=30pF, except on High Z and Low Z parameters, where C=5pF.



Package dimensions



	44-pin	TSOP 2			
	Min(mm)	Max(mm)			
A		1.2			
A ₁	0.05	0.15			
A ₂	0.95	1.05			
b	0.30	0.45			
c	0.12	0.21			
d	18.31	18.52			
\mathbf{E}_1	10.06	10.26			
E	11.68	11.94			
e	0.80 (typical)				
L	0.40	0.60			



	36-pin \$	SOJ 400					
	Min(mils)	Max(mils)					
A	0.128	0.148					
A ₁	0.025	_					
A ₂	0.105	0.115					
b	0.015	0.020					
b ₁	0.026	0.032					
c	0.007	0.013					
D	.920	.930					
e	0.045	0.055					
E	0.370 BSC						
$\mathbf{E_1}$	0.395	0.405					
$\mathbf{E_2}$	0.435	0.445					



Ordering codes

Package	Temperature	10 ns	12 ns	15 ns	20 ns
SOJ	Commercial	AS7C34096A-10JC	AS7C34096A-12JC	AS7C34096A-15JC	AS7C34096A-20JC
	Industrial	AS7C34096A-10JI	AS7C34096A-12JI	AS7C34096A-15JI	AS7C34096A-20JI
TSOP 2	Commercial	AS7C34096A-10TC	AS7C34096A-12TC	AS7C34096A-15TC	AS7C34096A-20TC
1301 2	Industrial	AS7C34096A-10TI	AS7C34096A-12TI	AS7C34096A-15TI	AS7C34096A-20TI

Note: Add suffix 'N' to the above part number for Lead Free Parts. (Ex: AS7C34096A - 10 TIN)

Part numbering system

AS7C	X	4096A	-XX	J orT	X	X
SRAM prefix	Voltage: 3 - 3.3V CMOS	Device number	Access time		Temperature ranges: C: Commercial, 0°C to 70°C I: Industrial, –40°C to 85°C	





Alliance Semiconductor Corporation 2575, Augustine Drive, Santa Clara, CA 95054 Tel: 408 - 855 - 4900

Fax: 408 - 855 - 4999

www.alsc.com

Copyright © Alliance Semiconductor All Rights Reserved Part Number: AS7C34096A Document Version: v. 2.1

© Copyright 2003 Alliance Semiconductor Corporation. All rights reserved. Our three-point logo, our name and Intelliwatt are trademarks or registered trademarks of Alliance. All other brand and product names may be the trademarks of their respective companies. Alliance reserves the right to make changes to this document and its products at any time without notice. Alliance assumes no responsibility for any errors that may appear in this document. The data contained herein represents Alliance's best data and/or estimates at the time of issuance. Alliance reserves the right to change or correct this data at any time, without notice. If the product described herein is under development, significant changes to these specifications are possible. The information in this product data sheet is intended to be general describetive information for potential customers and users, and is not intended to operate as, or provide, any guarantee or warrantee to any user or customer. Alliance does not assume any responsibility or liability arising out of the application or use of any product described herein, and disclaims any express or implied warranties related to the sale and/or use of Alliance products including liability or warranties related to fitness for a particular purpose, merchantability, or infringement of any intellectual property rights, except as express agreed to in Alliance's Terms and Conditions of Sale (which are available from Alliance). All sales of Alliance products are made exclusively according to Alliance's Terms and Conditions of Sale. The purchase of products from Alliance does not convey a license under any patent rights, copyrights; mask works rights, trademarks, or any other intellectual property rights of Alliance or third parties. Alliance does not authorize its products for use as critical components in life-supporting systems where a malfunction or failure may reasonably be expected to result in significant injury to the user, and the inclusion of Alliance products in such life-supporting system

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for SRAM category:

Click to view products by Alliance Memory manufacturer:

Other Similar products are found below:

CY6116A-35DMB CY7C1049GN-10VXI CY7C128A-45DMB GS8161Z36DD-200I GS88237CB-200I RMLV0408EGSB-4S2#AA0

IDT70V5388S166BG IS64WV3216BLL-15CTLA3 IS66WVE4M16ECLL-70BLI PCF8570P K6F2008V2E-LF70000 K6T4008C1B-GB70

CY7C1353S-100AXC AS6C8016-55BIN AS7C164A-15PCN 515712X IDT71V67603S133BG IS62WV51216EBLL-45BLI

IS63WV1288DBLL-10HLI IS66WVE2M16ECLL-70BLI IS66WVE4M16EALL-70BLI IS61WV102416DBLL-10TLI CY7C1381KV33
100AXC CY7C1381KVE33-133AXI 8602501XA 5962-3829425MUA 5962-3829430MUA 5962-8855206YA 5962-8866201YA 5962
8866204TA 5962-8866206MA 5962-8866208UA 5962-8872502XA 5962-9062007MXA 5962-9161705MXA GS882Z18CD-150I

M38510/28902BVA 8413202RA 5962-9161708MYA 5962-8871203XA 5962-8971202ZA 5962-8872501LA 5962-8866208YA 5962
8866205YA 5962-8866205UA 5962-8866203YA 5962-8855202YA 5962-8751309VA 5962-8687519XA IS61WV102416DBLL-10BLI